

PN8149H is a MOSFET driver IC with Hi-mode, Eco-mode, and Burst-mode. It features a soft drive function, EMI reduction, and a burst mode for high-frequency applications. The device is available in a DIP-8 package and is designed for use in power supplies and motor drives.

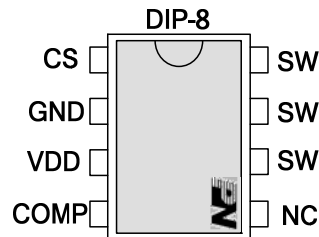
Key Features

- MOSFET driver
- Hi-mode 60kHz PWM
- Eco-mode 0.1 PFM
- Burst-mode 25kHz PWM
- EMI reduction
- Power dissipation < 75 mW @ 230VAC
- Efficiency > 90%
- Output current > 4A
- Input voltage 24V @ 85-265VAC
- Protection:
 - OTP
 - OLP
 - OVP

Pin Configuration

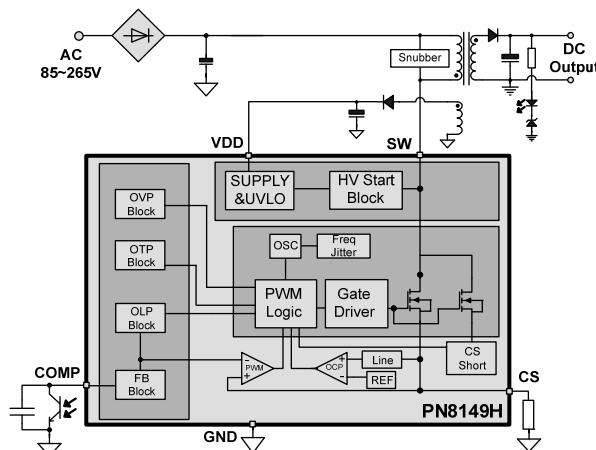
- VDD
- SW
- CS
- GND
- COMP

Package Information



Package	Part Number
DIP-8	PN8149HNEC-T1

Block Diagram



1Ñ7J Ê y

1Ñ7J =	1Ñ7J 7 '	1Ñ7J İ7- ýF
CS	1	+e#q õ#{ E7J
GND	2	`
VDD	3	Œ+e »EÄ • E7J
COMP	4	ýO, E7J
NC	5	0ª7J(Ő SW)
SW	6,7,8	Q »MOSFET%? ±7J

» İ).

x ñ » '	EÄ •+e »93 \$	öL ? ⁽¹⁾	0 n ? ⁽¹⁾
PN8149H	85~265 V _c	18W	24W

7# Ö

1. » İ). X öL)ß³ 45 ¼ 0 n? 45)ß³ ;#(B Ä

-L 93 \$

VDD 7J6@ » -0.3~30V 1ÑJ: Ö\$Y Ö- 100 -260
 CS,COMP 7J6@ » -0.3~5.5V 1>I' Lk R_{JC} - DIP-8 -40 /W
 SW 7J6@ » -0.3~800V E Q ?ESD 7- ,^UA HBM - -2kV
 5 \$Y Ö3 \$ -40~150 %? -79 â+e#qT_{pulse}=100uS 4A
 ÖY Ö3 \$ -55~150
 7# Ö1. xæ 1\ 9 Ø U I 9' 8ß(w4x ESD 7 ö(ESDA/JEDEC JDS-001-2014)#(B Ø ? ...#q0:F >|#(B -

+e"D(© W

(T_A = 25°C, V_{DD} = 15 V, L M 9B\$ >)

ò	1V'	' &	O ? I	" » I	O W I	... }
Ï)·G 6						
·)·1Ñ6@ »	BVDSS	I _{SW} = 1mA, T _J = 25	800	850		V
£ 1%?+e#q	I _{OFF}	V _{SW} = 700V, V _{COMP} = GND	20	45	60	uA
,FJ+eLk	R _{DS(on)}	I _{SW} = 1A, V _{COMP} = 3V, T _J = 25		2.5		

VDDC

ò	1V'	' &	0 ? I	" » I	0 W I	... }
BurstQ ?L8 I	V_{COMP_bm}	Voltage falling		1.2		V
BurstQ ?% L8 I	$V_{COMP_bm_hys}$	Voltage rising		1.3		V
COMP. D +e#q	I_{COMP}	$V_{COMP} = GND$		-200		uA
E:È> Ôö#{ &L\$	Td_olp			64		ms
G÷g"	AVCS			3.3		V/V
+e#q ö#{G 6						
E _ Ø&L\$	T_{SS}			8.5		ms
O ? ,FJ &L\$	T_{ON_MIN}			500		ns
É Ý&F &L\$	Td			150		ns
} "ï# ,LÀ&L\$	T_{LEB}			350		ns

7- yF

1. Ø

1.5mA+e#q
) FG V_{DD}+e ØF >| u+e ~ V_{DD}+e »Eî ' V_{DD} on ~
 8R(w O ß xQ » _ ØÑ!) V_{DD}+e Ø u+e ~
 _ Ø÷0;5 > ~ » Eµ 15 4ð) V_{DD}+e Ø
 7-Gÿ ~ t Ì 2 h i å +O '8R(w JF Qæ1 f
 Gý à_ Ø! & u+e+e#q j 0.6mA~

2. ð

8.5ms~
 8.5ms~

3. ËØ

PN8149H ÷+X H F, .7fi !5 . ~ FJE÷8*6,
 E~ *P; Ø- _ œl« j &L\$ ~ 'E† >, EMI(' W
 ...E† ~ 6G ~

4. 9*

PN8149H _9 N`) • * ° X 60kHz ~ MO F \$
 +eD F >|Aî5 ~ †(' 9;N`) • ~ Ø° _ ~ i .
 EMI(' W ~

5. Ø&

PN8149H _+e#q Q ? x f8R(w FJE÷ýO,7J+e
 »D µG K_Ufl# -(" E† ð< x f 0" ~

6. ð

35E
 35E
 V_{COMP}
 +e »CµE÷3.7V ~ 4ÿE÷ * ° 64ms &F &L\$ ~ O E Q
 ? ! ~

7. Ë

PN8149H L\$É Q ? ý? µj ~6G ~
 COE> ýE« ~ ýO,+e » ý? x COMP7J+e » ? ¼
 V_{COMP_bm} ~ » 1.2V ~ 8R(wF L\$!w Q ? ~
 ~)•1ÑE Ý~ COMP7JCµE÷V_{COMP_bm}100mV O
 E1Ñ %oIQ ,FJ ~F /ýN`) • x f #,L E«E> & ;
 ,N#N` ~

8. Ë

PN8149H 9F@ OE÷#q Ô~ O E+e#q
 FJE÷+e#q ð#{+eLk ð#{ ~ f FJE÷Aî ° Rcs+eLk
 F >|E÷#q Q&Ø;B38† ~

9. Ë

PN8149H _LJN` Q ? 'FJE÷ð{ COMP
 7J+e » ~XE«E> ...O"E> & ;L} ~ O EN`) • Q
 E«E> x) • ~ COMP7J+e » ? ¼_{COMP_Eco} ~ »
 2V ~ 8R(wF L)N` Q ? ~ O EN`) •L¿COE>
 L} ~6<L} ~ ~-\$8# O ?N`) •21.5kHz~

10. 45

PN8149H _E÷#q4i W> fl ~ X +e »93 \$ µ
)à 'E^ * ~) •L f ~

11. Ë

PN8149H _ì > fl ~ 6+e »K_Ufl ' —
 XG÷g+e#q ' : ~+X ¼i ·3+5 L)Øc ° W ~

12. ð

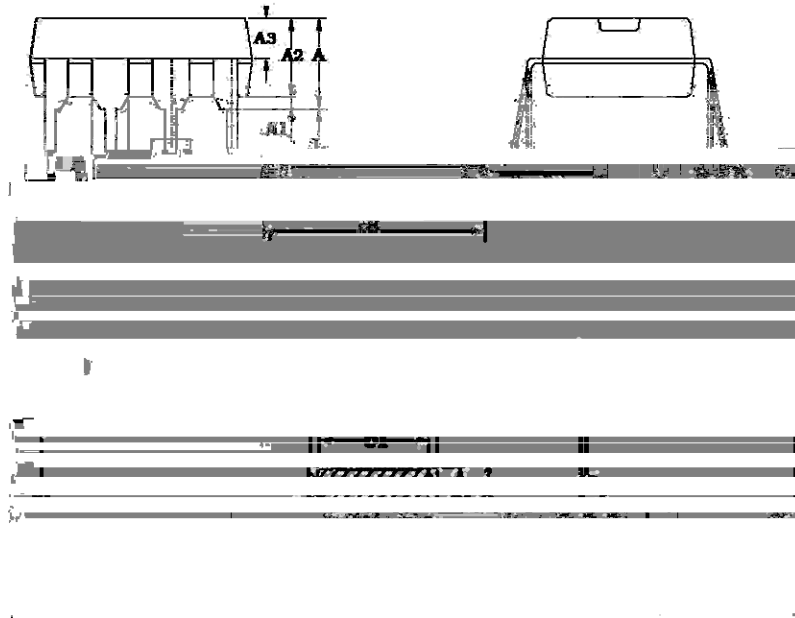
MOSFET ... x f8R(wLö@ X OC\$ fl ' x
 f+eD \$ C ¼ð#{MOSFET; \$Y Ö~ \$Y ÖµE÷
 150 ~8R(wF E÷\$Y Qæ1 ~

13. CS .DÔ

PN8149H _CS. D Ô~7- ~9 3+5 C\$
 j } ~ CS+eLk. D ~8R(wF CS. D Qæ1 ~
 X 2 h i å; ~)3+5 F >| Ô~

1>1

DIP-8 1



1V' \ J (OP (mm)	OWI (mm)	1V' \ J (OP (mm)	OWI (mm)
A	3.60	4.00	c1	0.23	0.27
A1	0.51		D	9.05	9.45
A2	3.00	3.40	E1	6.15	6.55
A3	1.55	1.65	e	2.54BSC	
b	0.44	0.53	e A	7.62BSC	

PN8149H

Chipown